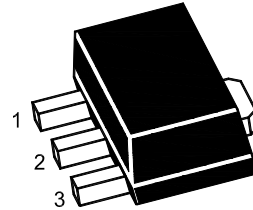


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- Power Transistor
- High Voltage and Current
- Low Collector-emitter saturation voltage
- Complements the 2SD1898U



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu\text{A}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-3\text{V}, I_C=-0.1\text{A}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-0.4	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		25		pF
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-50\text{mA}, f=30\text{MHz}$		100		MHz

CLASSIFICATION OF h_{FE}

RANK	P	Q	R
RANGE	82 - 180	120 - 270	180 - 390
MARKING	ZL		



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SOT-89

2SB1260U



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